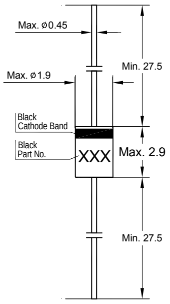
1N4531, 1N4532

Silicon Epitaxial Planar Switching Diode



Glass Case DO-34
Dimensions in mm

Applications

- High-speed switching

Absolute Maximum Ratings (T_a = 25 °C)

Parameter		Symbol	Value	Unit
Repetitive Peak Reverse Voltage		V_{RRM}	75	V
Continuous Reverse Voltage		V_R	75	V
Continuous Forward Current		I_F	200	mA
Repetitive Peak Forward Current		I_{FRM}	450	mA
Non-repetitive Peak Forward Current	at t = 1 µs at t = 1 ms at t = 1 s	I_{FSM}	4 1 0.5	A
Power Dissipation		P_{tot}	500	mW
Junction Temperature		T_j	200	°C
Storage Temperature Range		T_{stg}	- 65 to + 200	°C

Characteristics at T_a = 25 °C

Parameter		Symbol	Max.	Unit
Forward Voltage at I_F = 10 mA		V_F	1	V
Reverse Current				
at V_R = 20 V	1N4531	I_R	25	nA
at V_R = 50 V	1N4532	I_R	100	nA
at V_R = 20 V, T_j = 150 °C	1N4531	I_R	50	µA
at V_R = 50 V, T_j = 150 °C	1N4532	I_R	100	µA
Diode Capacitance at V_R = 0 , f = 1 MHz	1N4531	C_d	4	pF
	1N4532	C_d	2	pF
Reverse Recovery Time				
at I_F = 10 mA, I_R = 60 mA, R_L = 100 Ω	1N4531	t_{rr}	4	ns
	1N4532	t_{rr}	2	ns
at I_F = 10 mA, I_R = 10 mA, R_L = 100 Ω	1N4532	t_{rr}	4	ns

ISO/TS 16949 : 2009 Certificate No. 05103
ISO14001 : 2004 Certificate No. 7116
ISO 9001 : 2008 Certificate No. 0506098
BS-OHSAS 18001 : 2007 Certificate No. 7116
IECQ QC 080000 Certificate No. PRC-HSPM-1483-1

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